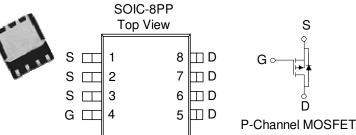
## P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe SOIC-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$		
-30	9 @ $V_{GS} = -10V$	-20		
	13 @ $V_{GS} = -4.5V$	-17		



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		$V_{DS}$	-30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
	T <sub>A</sub> =25°C	]   T_	-20		
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	-16	A	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	±50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-2.1	A	
	$T_A=25^{\circ}C$	D	5.0	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	PD	3.2		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
a	t <= 10 sec	r.	25	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>0JA</sub>	65	°C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM7433P

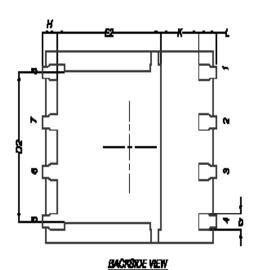
SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol Test Conditions	Limits			Unit		
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Ullit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \text{ uA}$	-30			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \text{ uA}$	-1			]	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	less	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Guirent	I <sub>DSS</sub>	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V$ , $V_{GS} = -10 V$	-50			Α	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, I_D = -2 \text{ A}$			9	mΩ	
Dialii-Source Off-Nesistance		$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$			13		
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		29		S	
Diode Forward Voltage	$V_{SD}$	$I_S = 2 A$ , $V_{GS} = 0 V$		-0.8		V	
Dynamic <sup>b</sup>						-	
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V},$		25			
Gate-Source Charge	$Q_{gs}$	$v_{DS} = -15 \text{ v}, v_{GS} = -5 \text{ v},$ $I_{D} = -2 \text{ A}$		11		nC	
Gate-Drain Charge	$Q_{gd}$	I <sub>D</sub> = -2 A		17			
Turn-On Delay Time	t <sub>d(on)</sub>			15			
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \ V, \ R_L = 6 \ \Omega$ ,		13		nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	ID = -1 A, VGEN = -10 V		100		1110	
Fall-Time	t <sub>f</sub>			54		1	

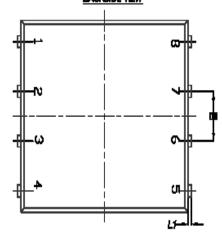
## Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

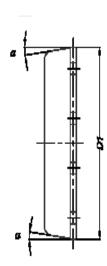
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## Package Information









Bu.	MOLLIMETERS			
DM.	MON.	MOM.	MAX	
A	0.90	1.00	1.10	
Þ	0.33	0.41	0.61	
C	0.20	0.25	0.30	
D1	4.80	4.90	5.00	
D2	281	2.81	198	
Ε	5.90	6.00	6.10	
Ef	5.70	6.76	5.80	
<i>E</i> 2	8.36	3.58	278	
Θ	1.27 88C			
H	0.41	0.61	0.81	
K	1.10	•	•	
Ĺ	0.51	0.67	0.71	
L1	0.06	0.13	0.20	
Œ	ď	-	12*	